



SET study on Actel FPGAs

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Goal

 Analysis of the robustness of designs implemented on Flash-based FPGAs against Single Event Transients

Outline

- Collaborations
- Flash-based FPGAs
- Radiation effects on Flash-based FPGAs
- The SET analysis flows
 - Measurement of the SET pulses
 - Analysis of the configuration memory
 - Modeling the Versatile logic
- Experimental results
- Status of the work

Collaborations

Actel Corporation



Flash-based FPGAs

- Flash-based Field Programmable Gate Arrays (FPGAs) consist of:
 - Configuration memory of Flash-cells
 - Programmable logic blocks (VersaTiles)
 - Programmable interconnections



Radiation effects on Flashbased FPGAs

Charge-leakage in the floating gate

- Total Ionizing Dose (TID) lead degradation on switch threshold voltage (V_{TH})
- Single Event Transients (SETs)
 - High charged particles cross the logic and interconnections element

SETs effects on Flash-based FPGAs

- Effect on Sensitive node (i.e. logic gate)
- Effect in the logic configured as a latch
 SET turns into a SEU (due to the feedback path)
- Effect in the floating gate switch
 - Effects may generate an SET into the logic / routing of the implemented circuit
 - Floating gate technology characteristics
 - Logic / Interconnection switch layout.

The SET analysis flows

- Current development of analysis at multiple targets of the SET incidence on Actel
 Flash-based FPGAs
 - Measurement of SET pulses
 - Configuration memory
 - Logic / Interconnection model

Measurement of the SET pulses

• The effect of an SET is mainly due to:

- Location
- Arrival time
- Pulse's width.



Infinite number of combinations





The proposed methodology



The DUT Design



The Monitoring Design



Analysis of the configuration memory

Analysis of the original bitstream format

- Finding the rows of tiles
- Logical to physical mapping process
- Logic resources allocation
- Analysis of the logic / interconnection topology
- Static Analyzer tool for the estimation of SET sensitiveness
 - First release validated on logic resources

An example: tile [0,15]

The provide the second seco



An example: tile [0,15]



The column 15 locate the *block* in the frame: 15 mod 4=3 all the *blocks* that program the tile are in position: $(0+i^{*}4)$ when i $\in [0-43]$



43

An example: tile [0,15] The Mapping



Modeling the Versatile logic

- VHDL / Spice model of the Versatile cell
- Functional analysis
 - Fault injection of SET within the model



Redundant configuration point

A case study

- DUT: Actel ProASIC3 250
 - 6,144 VersaTiles
 - A single chain composed of 5,652 inverters
 - 8 channels, $\Delta T = 3.84$ ns
 - 8 channels, ΔT = 0.96 ns
- MD: Xilinx Virtex-II Pro 4
 - 100 MHz clock \rightarrow blind time \approx 20 ns
 - Partial readback capability
 - Full support for 11.49 IEEE standard (Boundary Scan)
- Ion beams: Cyclotron Louvain-la-Neuve
 - Xe ions, LET = 5.59E+01 MeV·cm²/mg, fluency = 1.00·10⁶ particles/cm²
 - Ar ions, LET = 1.41E+01 MeV·cm²/mg, fluency = 3.00·10⁶ particles/cm²

Measurement of SET pulses

- Broadening effects among the DUT circuit
- Widening effects dependent on the number of gates

Event [#] – DUT with 4,500 inverters



Measurement of SET pulses

- Broadening effects among the DUT circuit
- Widening effects dependent on the number of gates

Event [#] – DUT with 1,000 inverters



- Analysis of the configuration memory
 - Logic resources have been individuated
 - Interconnections rules are under development
- Logic sensitive locations computed and measured accordingly
 - LET [Xenon] of 5.59E+01 MeV·cm²/mg
 - LET [Argon] of 1.41E+01 MeV·cm²/mg

Circuit	Ion	Sensitive location [#]	Used Tiles [#]	Measured SET [#]
450	Xe	6,664	903	20
1000	Xe	12,538	1,632	42

The proportional coefficient between sensitive locations and the measured SET is approximately 333 for Xe ion and about 1,332 in the case of the Ar ion.

The ratio between the two proportional coefficients (1,332 / 333 = 4) is almost equivalent to the ratio between the energy transferred to the device (LET[Xe] / LET[Ar]) = 3.96.

Oynamic test

- Pipelined multiplier 16-bits and 35-stages
- Running frequency: 40 MHz
- 20 runs

Two mapping with different routing

- 136,555 configured bits: 105 average observed SET/SEU
- 228,263 configured bits: 114 average observed SET/SEU

Static test

- Shift registers16-bits and 35-stages
- 14 runs for each circuit

Two circuits with different initial condition

- 1 -> 0 36 observed SEU
- 0 -> 1 52 observed SEU

- Modeling the VersaTile
- Different mapping lead to a decrease of about 56% of fault bits on the average



Status of the work

- SET measurement
 - Static and Dynamic test with different running frequency
 - Different gates sensitivity
- Configuration memory
 - Logic elements : stable
 - Interconnections hierarchy : on going
- VersaTile model
 - Integrating redundant function into an automatic mapper tool : on going

Thank you...

For questions and comments,

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